

4N35X, 4N36X, 4N37X,  
4N35, 4N36, 4N37,



**OPTICALLY COUPLED  
ISOLATOR  
PHOTOTRANSISTOR OUTPUT**

**APPROVALS**

- UL recognised, File No. E91231

**'X' SPECIFICATION APPROVALS**

- VDE0884 in 3 available lead forms :-  
- STD  
- G form  
- SMD approved to CECC 00802
- BSI approved - Certificate No. 8001

**DESCRIPTION**

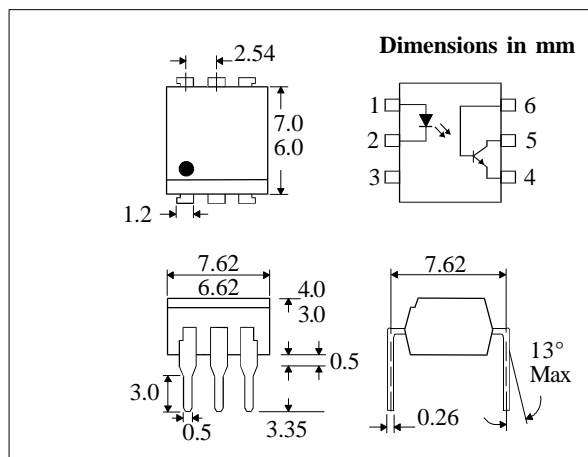
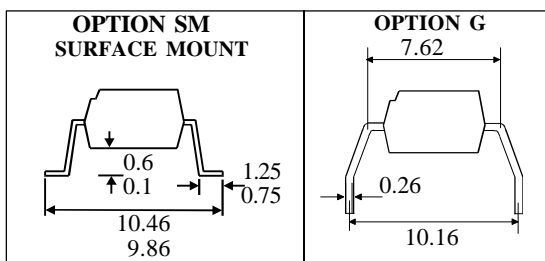
The 4N35, 4N36, 4N37 series of optically coupled isolators consist of infrared light emitting diode and NPN silicon photo transistor in a standard 6 pin dual in line plastic package.

**FEATURES**

- Options :-  
10mm lead spread - add G after part no.  
Surface mount - add SM after part no.  
Tape&reel - add SMT&R after part no.
- High Current Transfer Ratio (100% min.)
- High Isolation Voltage (5.3kV<sub>RMS</sub>, 7.5kV<sub>PK</sub>)
- All electrical parameters 100% tested
- Custom electrical selections available

**APPLICATIONS**

- DC motor controllers
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances



**ABSOLUTE MAXIMUM RATINGS  
(25°C unless otherwise specified)**

Storage Temperature	-55°C to +150°C
Operating Temperature	-55°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

**INPUT DIODE**

Forward Current	60mA
Reverse Voltage	6V
Power Dissipation	105mW

**OUTPUT TRANSISTOR**

Collector-emitter Voltage $BV_{CEO}$	30V
Collector-base Voltage $BV_{CBO}$	70V
Emitter-collector Voltage $BV_{ECO}$	6V
Power Dissipation	160mW

**POWER DISSIPATION**

Total Power Dissipation	200mW
(derate linearly 2.67mW/°C above 25°C)	

**ISOCOM COMPONENTS LTD**  
Unit 25B, Park View Road West,  
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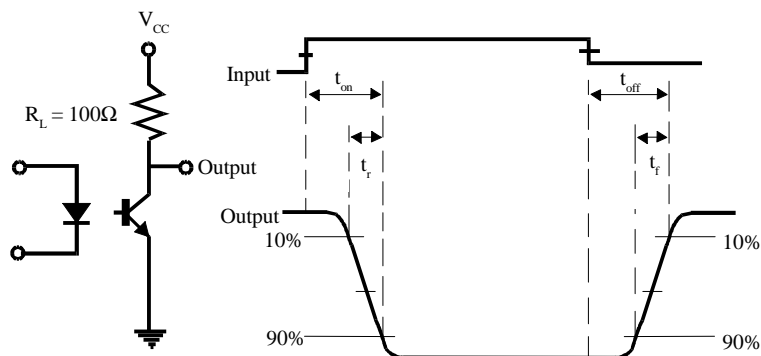
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Allen, TX 75002 USA  
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**ELECTRICAL CHARACTERISTICS (  $T_A = 25^\circ\text{C}$  Unless otherwise noted )**

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage ( $V_F$ )		1.2	1.5	V	$I_F = 10\text{mA}$
	Reverse Current ( $I_R$ )			10	$\mu\text{A}$	$V_R = 6\text{V}$
Output	Collector-emitter Breakdown ( $BV_{CEO}$ ) ( Note 2 )	30			V	$I_C = 1\text{mA}$
	Collector-base Breakdown ( $BV_{CBO}$ )	70			V	$I_C = 100\mu\text{A}$
	Emitter-collector Breakdown ( $BV_{ECO}$ )	6			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current ( $I_{CEO}$ )			50	nA	$V_{CE} = 10\text{V}$
	Collector-base Dark Current ( $I_{CBO}$ )			20	nA	$V_{CE} = 10\text{V}$
Coupled	Current Transfer Ratio (CTR)	100			%	$10\text{mA } I_F, 10\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.3	V	$10\text{mA } I_F, 0.5\text{mA } I_C$
	Input to Output Isolation Voltage $V_{ISO}$	5300 7500			$V_{RMS}$ $V_{PK}$	See note 1 See note 1
	Input-output Isolation Resistance $R_{ISO}$	$5 \times 10^{10}$			$\Omega$	$V_{IO} = 500\text{V}$ (note 1)
	Turn-on Time $t_{on}$		5	10	$\mu\text{s}$	$V_{CC} = 10\text{V},$ $I_C = 2\text{mA}, R_L = 100\Omega$ ( FIG 1 )
	Turn-off Time $t_{off}$		5	10	$\mu\text{s}$	
	Output Rise Time $t_r$		3.5		$\mu\text{s}$	
Output Fall Time $t_f$		4.9		$\mu\text{s}$		

Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

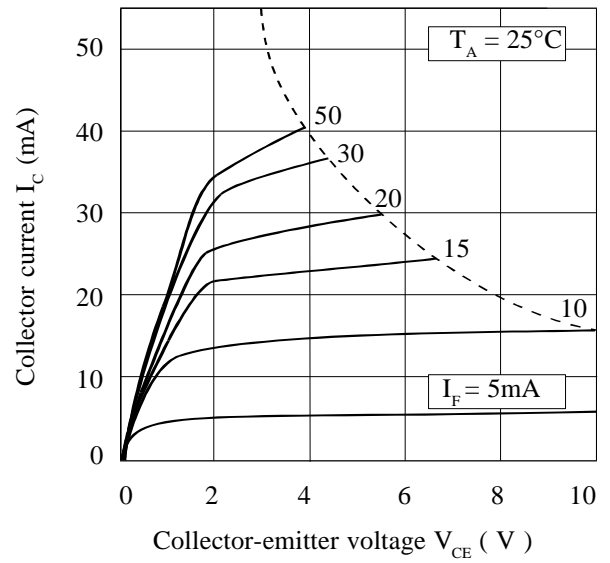


**FIG 1**

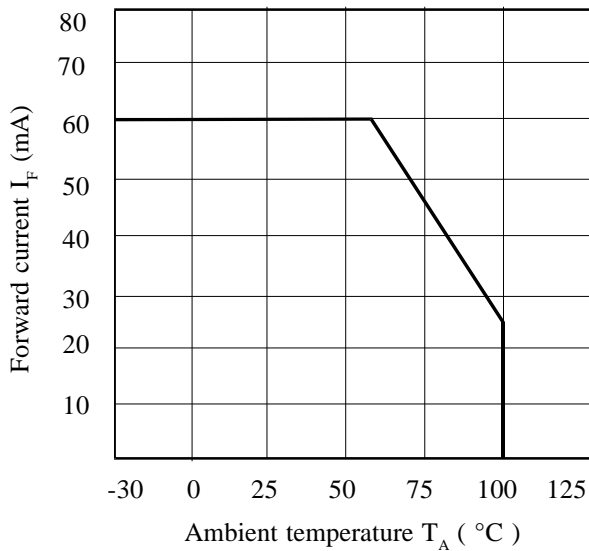
**Collector Power Dissipation vs. Ambient Temperature**



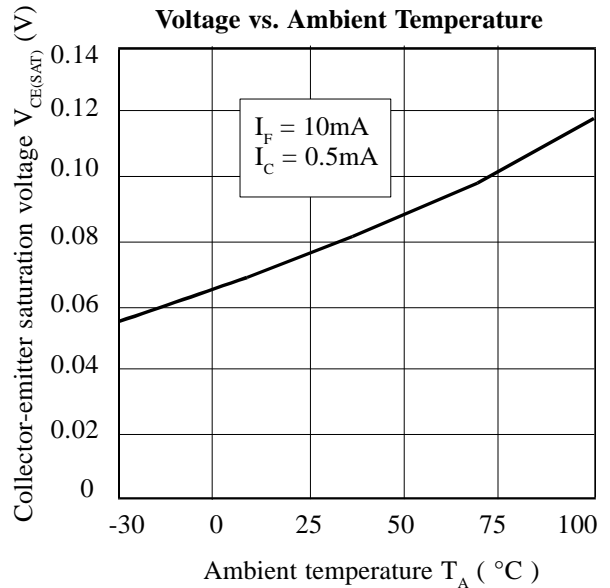
**Collector Current vs. Collector-emitter Voltage**



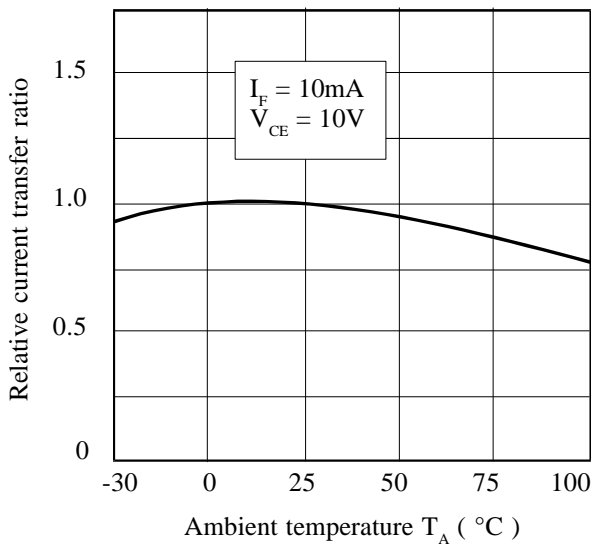
**Forward Current vs. Ambient Temperature**



**Collector-emitter Saturation Voltage vs. Ambient Temperature**



**Relative Current Transfer Ratio vs. Ambient Temperature**



**Relative Current Transfer Ratio vs. Forward Current**

